

Alpha & Omega Semiconductor Product Reliability Qualification Report

AOLF66910Q rev A

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This report delineates the product's quality and reliability test outcomes. Specific sample sizes undergo accelerated environmental tests, with corresponding electrical testing before and after each interval. Analysis of the conclusive electrical test results affirms the product's adherence to AOS quality and reliability standards in accordance with **AEC-Q101-Rev-E**. Reference to the existing qualification outcomes for similar products is warranted due to structural similarities. The released product will be classified by its process family and undergo regular monitoring to ensure continual enhancements in product quality.

I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Duration	Lots/SS	Number of Failures	Reference Standard
HTGB <i>High Temperature Gate Bias</i>	175°C Vgs=100% of Vgsmax	1000 hrs	3 * 77	0/231	JESD22-A108
HTRB <i>High Temperature Reverse Bias</i>	175°C Vds=100% of Vdsmax	1000 hrs	3 * 77	0/231	JESD22-A108
PC <i>Precondition</i>	168 hrs, 85°C, 85%RH, 3 cycles reflow @ 260°C (MSL 1)	-	15 * 77	0/1155	JESD22-A113 J-STD-020
HAST* <i>Highly Accelerated Stress Test</i>	130°C, 85%RH, Vds = 80% of Vdsmax up to 42V	96 hrs	3 * 77	0/231	JESD22-A110
H3TRB* <i>High Humidity High Temperature Reverse Bias</i>	85°C, 85%RH, Vds = 80% of Vdsmax up to 100V	1000 hrs	3 * 77	0/231	JESD22-A101
AC* <i>Autoclave</i>	121°C, 100%RH, 15psig	96 hrs	3 * 77	0/231	JESD22-A102
TC* <i>Temperature Cycling</i>	-55°C to 150°C, air to air	1000 cycles	3 * 77	0/231	JESD22-A104
IOL* <i>Intermittent Operational Life</i>	$\Delta T_j = 100^\circ\text{C}$ $t_{on} = 2 \text{ minutes}$ $t_{off} = 2 \text{ minutes}$	15000 cycles	3 * 77	0/231	MIL-STD-750 Method 1037
RSH <i>Resistance to Solder Heat</i>	260°C	10 sec	1 * 30	0/30	JESD22-A111 (SMD)
ESD_HBM	Class H2 (>2000V to ≤4000V)	-	30 pcs	-	AEC-Q101-001
ESD_CDM	Class C3 (≥1000V)	-	30 pcs	-	AEC-Q101-005
DPA <i>Destructive Physical Analysis</i>	Random sample of parts that have successfully completed H3TRB or HAST, and TC	-	3 * 2	0/6	AEC-Q101-004
PV <i>Parametric Verification</i>	Tj= -55°C ,25°C ,175°C	-	75 pcs	0/75	Datasheet

Notes:

* For SMD devices reliability stress tests performed after PC (precondition).

II. Reliability Evaluation

FIT rate (per billion): 2.61

MTTF = 43670 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

At 60% Confidence Level

Failure Rate = $\text{Chi}^2 \times 10^9 / [2 (N) (H) (A_f)] = 2.61$

MTTF = $10^9 / \text{FIT} = 43670$ years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from burn-in tests

H = Duration of burn-in testing

A_f = Acceleration Factor from Test to Use Conditions ($E_a = 0.7\text{eV}$ and $T_{J u} = 55^\circ\text{C}$)

Acceleration Factor **[A_f]** = $\text{Exp} [E_a / k (1/T_{J u} - 1/T_{J s})]$

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	125 deg C	150 deg C	175 deg C
A_f	758	256	95	38	9.7	2.9	1

T_{J s} = Stressed junction temperature in degree (Kelvin), $K = C + 273.16$

T_{J u} = The use junction temperature in degree (Kelvin), $K = C + 273.16$

k = Boltzmann's constant, $8.617164 \times 10^{-5}\text{eV} / K$